

Title (en)

PHOTOELECTRIC TRANSDUCER AND PRODUCTION METHOD THEREFOR

Title (de)

FOTOELEKTRISCHER WANDLER UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

ÉLÉMENT DE CONVERSION PHOTOÉLECTRIQUE, ET PROCÉDÉ DE FABRICATION DE CELUI-CI

Publication

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Application

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Abstract (en)

Provided is a photoelectric conversion element (10) which suppresses the generation of a reverse current and which has enhanced photoelectric conversion efficiency. The photoelectric conversion element (10) according to the present invention includes at least one support (1), conductive layer (2), photoelectric conversion layer (3), porous insulating layer (4), catalyst layer (5), counter conductive layer (6), and counter support (8) in series. The photoelectric conversion layer (3) includes a porous semiconductor sub-layer containing a semiconductor material and a photosensitizing element adsorbed on the porous semiconductor sub-layer. A carrier transport material (9) is placed between the porous insulating layer (4) and the catalyst layer (5). The porous semiconductor sub-layer and the porous insulating layer (4) contain pores. The pores are filled with the carrier transport material (9). There is no strong bonding force, obtained by deposition by a screen printing process, a vapor deposition process, or a sputtering process, between the porous insulating layer (4) and the catalyst layer (5).

IPC 8 full level

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